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Focus Issue on Oxide Thin Film Transistors



Table of Contents**Commentary****Introduction to the Focus Issue on Oxide Thin Film Transistors***Yue Kuo, Mamoru Furuta Y5***Electronic and Photonic Devices, and Systems****Density of States in Amorphous In-Ga-Zn-O Thin-Film Transistor under Negative Bias Illumination Stress***Yoshihiro Ueoka, Yasuaki Ishikawa,
Juan Paolo Bermundo, Haruka Yamazaki,
Satoshi Urakawa, Mami Fujii, Masahiro Horita,
Yukiharu Uraoka Q3001***Channel Composition Effect on the Bias-Illumination-Stress Stability of Solution-Processed Transparent Oxide Thin-Film Transistors Using Amorphous Aluminum-Indium-Zinc-Oxide Channel Layers***Min-Ji Park, Jun-Yong Bak, Jeong-Seon Choi,
Sung-Min Yoon Q3005***In-Ga-Zn-Oxide Semiconductor and Its Transistor Characteristics***Shunpei Yamazaki, Tomoaki Atsumi, Koji Dairiki,
Kenichi Okazaki, Noboru Kimizuka Q3012***Quantitative Analysis of Hole-Trapping and Defect-Creation in InGaZnO Thin-Film Transistor under Negative-Bias and Illumination-Stress***Mai Phi Hung, Dapeng Wang, Tasuya Toda,
Jingxin Jiang, Mamoru Furuta Q3023***Mobility Assessment of Depletion-Mode Oxide Thin-Film Transistors Using the Comprehensive Depletion-Mode Model***Fan Zhou, Bao-Sung Yeh, Kevin A. Archila,
John F. Wager Q3027***Impact of Annealing on Contact Formation and Stability of IGZO TFTs***T. Mudgal, N. Walsh, R. G. Manley, K. D. Hirschman Q3032***2014 • Volume 3
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Fabrication of Flexible Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors by a Chemical Vapor Deposition-Free Process on Polyethylene Napthalate*Hua Xu, Jiawei Pang, Miao Xu, Min Li, Ying Guo,
Zikai Chen, Lang Wang, Jianhua Zou, Hong Tao,
Lei Wang, Junbiao Peng Q3035***Film Texture, Hole Transport and Field-Effect Mobility in Polycrystalline SnO Thin Films on Glass***Po-Ching Hsu, Chung-Chih Wu, Hidenori Hiramatsu,
Toshio Kamiya, Hideo Hosono Q3040***Role of Self-Assembled Monolayers on Improved Electrical Stability of Amorphous In-Ga-Zn-O Thin-Film Transistors***Xiaosong Du, Brendan T. Flynn, Joshua R. Motley,
William F. Stickle, Hendrik Bluhm,
Gregory S. Herman Q3045***Vapor-Induced Improvements in Field Effect Mobility of Transparent a-IGZO TFTs***Mami N. Fujii, Yasuaki Ishikawa, Masahiro Horita,
Yukiharu Uraoka Q3050***InZnSnO-Based Electronic Devices for Flat Panel Display Applications***Po-Tsun Liu, Chur-Shyang Fuh, Yang-Shun Fan,
S. M. Sze Q3054***Review of Present Reliability Challenges in Amorphous In-Ga-Zn-O Thin Film Transistors***Tien-Yu Hsieh, Ting-Chang Chang, Te-Chih Chen,
Ming-Yen Tsai Q3058***The Time Response of the On-Current for the Amorphous In-Ga-Zn-O Thin Film Transistor to the Illumination Pulse***Ya-Hsiang Tai, Chun-Yi Chang, Ya-Wei Chen,
Yi-Jung Chen Q3071***Sensitivity Evaluation on Amorphous InGaZnO₄ Thin-Film Transistor pH Sensors Having Various Capacitances of Ion-Sensitive and Bottom-Gate Insulators***Kazushige Takechi, Shinnosuke Iwamatsu, Toru Yahagi,
Yutaka Abe, Seiya Kobayashi, Hiroshi Tanabe Q3076*

**Effects of Solvent Treatment on the Characteristics
of InGaZnO Thin-Film Transistors**

*Peng Xiao, Linfeng Lan, Ting Dong, Zhenguo Lin,
Lei Wang, Honglong Ning, Junbiao Peng Q3081*

**Roles of Hydrogen in Amorphous Oxide
Semiconductor In-Ga-Zn-O: Comparison of
Conventional and Ultra-High-Vacuum Sputtering**

*Takaya Miyase, Ken Watanabe, Isao Sakaguchi,
Naoki Ohashi, Kay Domen, Kenji Nomura,
Hidenori Hiramatsu, Hideya Kumomi,
Hideo Hosono, Toshio Kamiya Q3085*

**Magnetron-Sputtered SnO Thin Films for p-Type
and Ambipolar TFT Applications**

H. Luo, L. Y. Liang, Q. Liu, H. T. Cao Q3091